## Computational Microelectronics Report (Homework #5)

Professor: Hong, Sung-Min

Major: Electrical Engineering and Computer Science

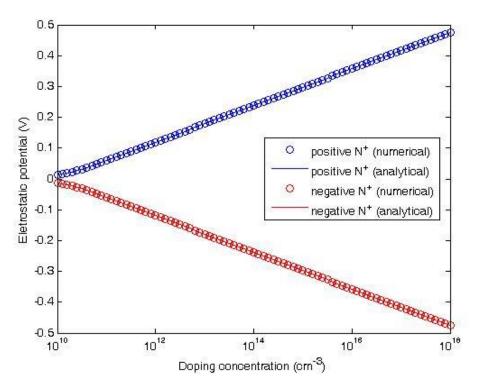
Student Number: 20181018

Student Name: Jang, Mi

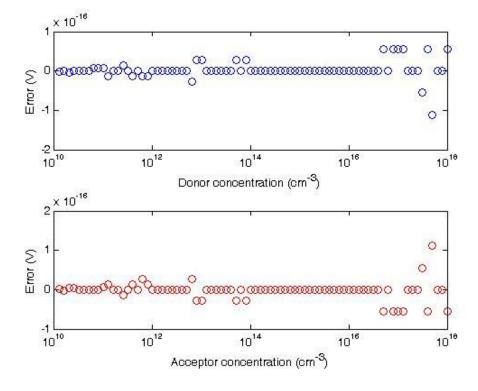
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1. Electrostatic potential – Doping density (Positive N+: Donor, Negative N+: Acceptor) Number of repetition: 1000, Initial value of  $\emptyset$ :  $\pm 1V$ 



2. Difference between numerical solution and analytic solution as a function of dopant density



There is no significant difference between the values obtained through Newton-Raphson method and those obtained though analytic method.